MOSFET – N-Channel

80 V, 2.9 mΩ**, 175 A**

Features

- Low On–Resistance
- High Current Capability
- 100% Avalanche Tested
- ATPAK Package is Pin-compatible with DPAK (TO-252)
- Pb-Free, Halogen Free and RoHS Compliance

Typical Applications

- Multi Lib Protection
- Motor Control

Specifications

Table 1. ABSOLUTE MAXIMUM RATING at T_A = $25^\circ C$

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Parameter	Symbol	Value	Unit	
Drain to Source Voltage	V _{DSS}	80	V	
Gate to Source Voltage	V _{GSS}	±20	V	
Drain Current (DC)	Ι _D	175	А	
Drain Current (Pulse) PW ≤ 10 ms, Duty Cycle ≤ 1%	I _{DP}	600	A	
Power Dissipation $T_{\rm C}$ = 25°C	P _D	90	W	
Operating Junction and Storage Temperature	T _J , T _{STG}	–55 to +150	°C	
Single Pulse Drain to Source Avalanche Energy (L = 0.1 mH, I _{L(pk)} = 55 A)	E _{AS}	151	mJ	
Lead Temperature for Soldering Purposes, 3 mm from Case for 10 seconds	ΤL	260	°C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Table 2. THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit	
Junction to Case Steady State ($T_C = 25^{\circ}C$)	$R_{\theta JC}$	1.38	°C/W	
Junction to Ambient (Note 1)	$R_{\theta JA}$	77.2	°C/W	

1. Surface mounted on FR4 board using a 130 mm², 1 oz. Cu pad.

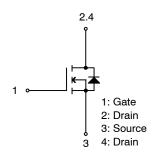


ON Semiconductor®

www.onsemi.com

V _{DSS}	R _{DS} (on) Max	I _D Max
80 V	2.9 mΩ @ 10V	175 A

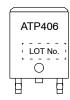
ELECTRICAL CONNECTION N-Channel





DPAK / ATPAK CASE 369AM

MARKING DIAGRAM



ORDERING INFORMATION

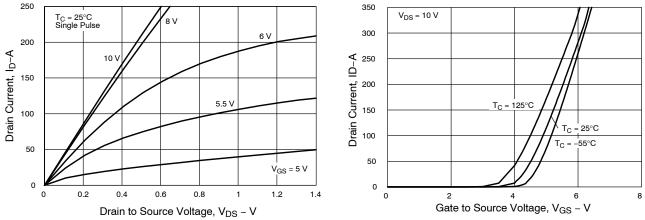
See detailed ordering and shipping information on page 6 of this data sheet.

Table 3. ELECTRICAL CHARACTERISTICS at T_{A} = $25^{\circ}C$

			Value			
Parameter	Symbol	Conditions	min typ		max	Unit
Drain to Source Breakdown Voltage	V(_{BR}) _{DSS}	I _D = 1 mA, V _{GS} = 0 V	80			V
Zero-Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 80 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			10	μA
Gate to Source Leakage Current	I _{GSS}	V_{GS} = ±20 V, V_{DS} = 0 V			±100	nA
Gate Threshold Voltage	V _{GS} (th)	V _{DS} = 10 V, I _D = 1 mA	2.0		4.0	V
Forward Transconductance	9 _{FS}	V _{DS} = 10 V, I _D = 50 A		185		S
Static Drain to Source On-State Resistance	R _{DS} (on)	I _D = 50 A, V _{GS} = 10 V		2.2	2.9	mΩ
Input Capacitance	C _{ISS}	V _{DS} = 40 V, f = 1 MHz		8040		pF
Output Capacitance	C _{OSS}			1120		pF
Reverse Transfer Capacitance	C _{RSS}			40		pF
Turn-ON Delay Time	t _d (on)	$V_{GS} = 10 \text{ V}, V_{DS} = 48 \text{ V}, \\ I_D = 50 \text{ A}, \text{ R}_G = 50 \Omega, \\ \label{eq:VGS}$		77		ns
Rise Time	t _r			420		ns
Turn-OFF Delay Time	t _d (off)			310		ns
Fall Time	t _f			155		ns
Total Gate Charge	Q _G	V _{DS} = 48 V, V _{GS} = 10 V,		110		nC
Gate to Source Charge	Q _{GS}	I _D = 50 A		32.4		nC
Gate to Drain "Miller" Charge	Q _{GD}	1 1		31.8		nC
Forward Diode Voltage	V _{SD}	I _S = 100 A, V _{GS} = 0 V		0.9	1.5	V
Reverse Recovery Time	t _{RR}	$I_{\rm S} = 50$ A, $V_{\rm GS} = 0$ V,		90		ns
Reverse Recovery Charge	Q _{RR}	d _l /dt = 100 A/μs		126		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS







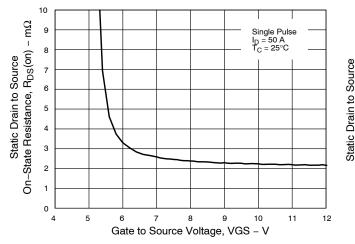


Figure 3. On–Resistance vs. Gate to Source Voltage

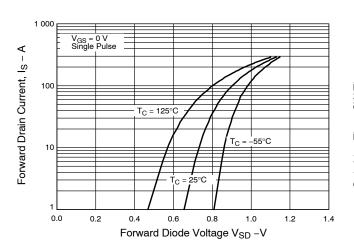


Figure 5. Diode Forward Voltage vs. Current

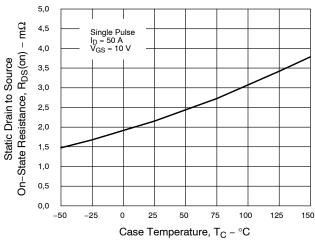


Figure 4. On-Resistance vs. Case Temperature

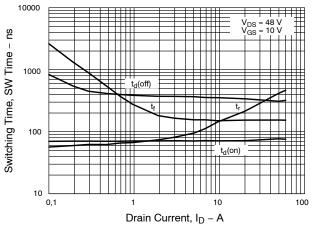


Figure 6. Switching Time vs. Drain Current

TYPICAL CHARACTERISTICS (continued)

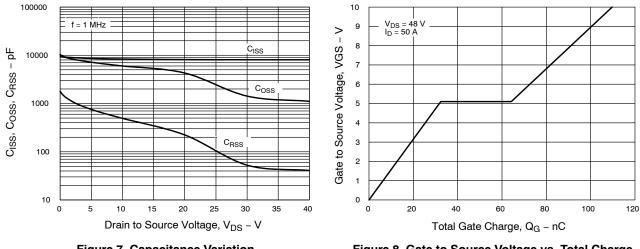
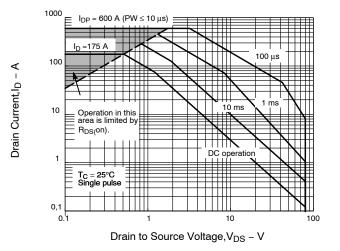




Figure 8. Gate to Source Voltage vs. Total Charge





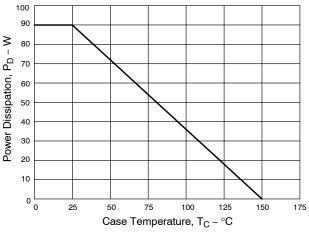


Figure 10. Power Dissipation vs. Case Temperature

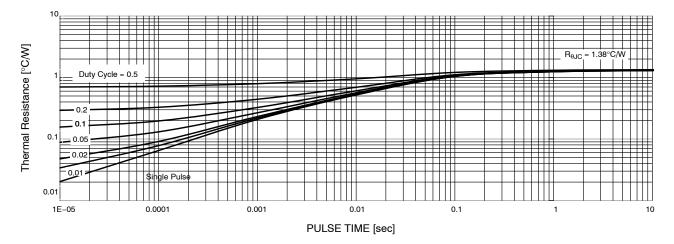
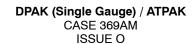
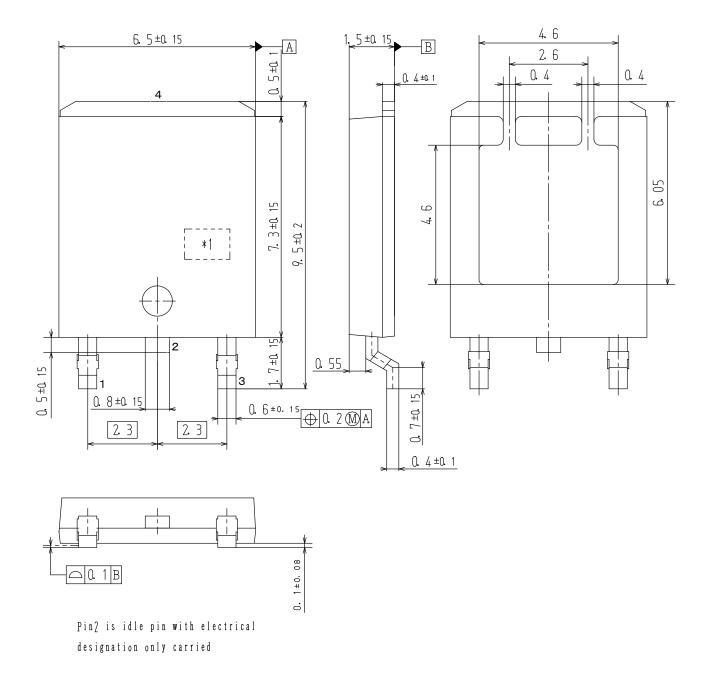


Figure 11. Thermal Response





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